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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	216
Number of Logic Elements/Cells	1728
Total RAM Bits	12288
Number of I/O	147
Number of Gates	69000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k30aqc208-1

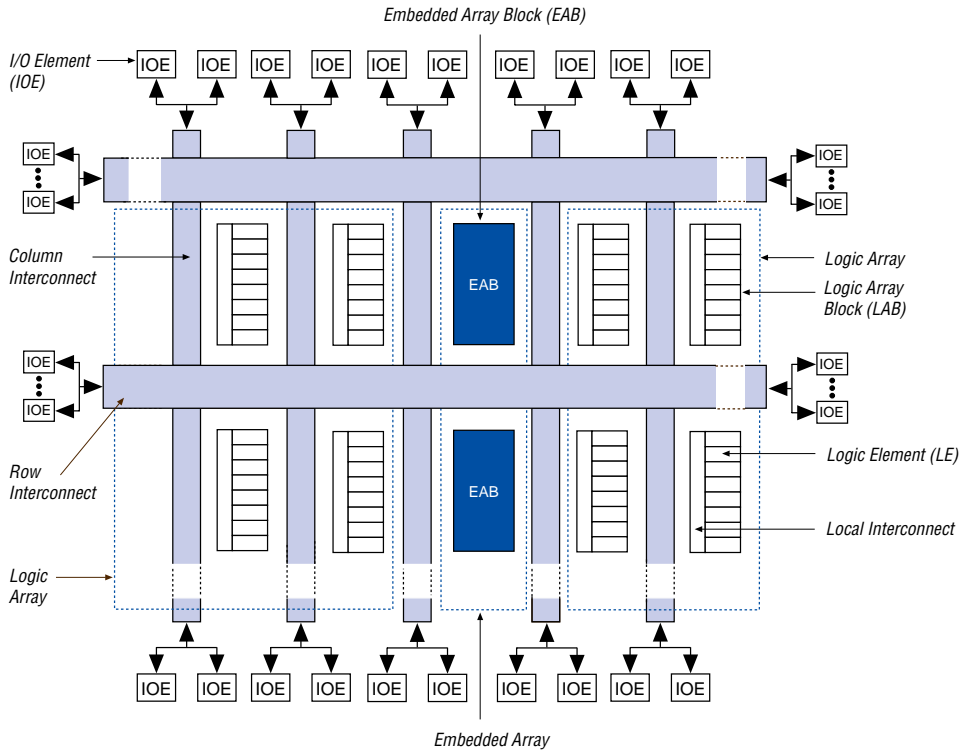
Table 4. FLEX 10K Package Options & I/O Pin Count *Note (1)*

Device	84-Pin PLCC	100-Pin TQFP	144-Pin TQFP	208-Pin PQFP RQFP	240-Pin PQFP RQFP
EPF10K10	59		102	134	
EPF10K10A		66	102	134	
EPF10K20			102	147	189
EPF10K30				147	189
EPF10K30A			102	147	189
EPF10K40				147	189
EPF10K50					189
EPF10K50V					189
EPF10K70					189
EPF10K100					
EPF10K100A					189
EPF10K130V					
EPF10K250A					

Table 5. FLEX 10K Package Options & I/O Pin Count (Continued) *Note (1)*

Device	503-Pin PGA	599-Pin PGA	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	600-Pin BGA	403-Pin PGA
EPF10K10							
EPF10K10A			150		150 (2)		
EPF10K20							
EPF10K30				246			
EPF10K30A			191	246	246		
EPF10K40							
EPF10K50				274			310
EPF10K50V				274			
EPF10K70	358						
EPF10K100	406						
EPF10K100A				274	369	406	
EPF10K130V		470				470	
EPF10K250A		470				470	

Figure 1. FLEX 10K Device Block Diagram



FLEX 10K devices provide six dedicated inputs that drive the flipflops' control inputs to ensure the efficient distribution of high-speed, low-skew (less than 1.5 ns) control signals. These signals use dedicated routing channels that provide shorter delays and lower skews than the FastTrack Interconnect. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or an internally generated asynchronous clear signal that clears many registers in the device.

Embedded Array Block

The EAB is a flexible block of RAM with registers on the input and output ports, and is used to implement common gate array megafunctions. The EAB is also suitable for functions such as multipliers, vector scalars, and error correction circuits, because it is large and flexible. These functions can be combined in applications such as digital filters and microcontrollers.

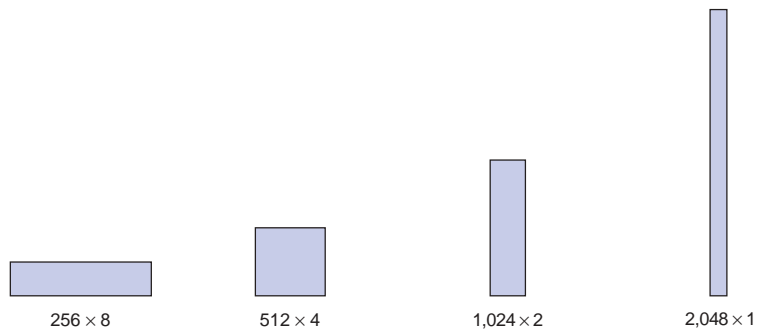
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4×4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (\overline{WE}) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the \overline{WE} signal. In contrast, the EAB's synchronous RAM generates its own \overline{WE} signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256×8 , 512×4 , $1,024 \times 2$, or $2,048 \times 1$. See [Figure 2](#).

Figure 2. EAB Memory Configurations



Up/Down Counter Mode

The up/down counter mode offers counter enable, clock enable, synchronous up/down control, and data loading options. These control signals are generated by the data inputs from the LAB local interconnect, the carry-in signal, and output feedback from the programmable register. The Up/down counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading. Data can also be loaded asynchronously with the clear and preset register control signals, without using the LUT resources.

Clearable Counter Mode

The clearable counter mode is similar to the up/down counter mode, but supports a synchronous clear instead of the up/down control. The clear function is substituted for the cascade-in signal in the up/down counter mode. Clearable counter mode uses 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. Synchronous loading is provided by a 2-to-1 multiplexer. The output of this multiplexer is ANDed with a synchronous clear signal.

Internal Tri-State Emulation

Internal tri-state emulation provides internal tri-stating without the limitations of a physical tri-state bus. In a physical tri-state bus, the tri-state buffers' output enable (OE) signals select which signal drives the bus. However, if multiple OE signals are active, contending signals can be driven onto the bus. Conversely, if no OE signals are active, the bus will float. Internal tri-state emulation resolves contending tri-state buffers to a low value and floating buses to a high value, thereby eliminating these problems. The Altera software automatically implements tri-state bus functionality with a multiplexer.

Clear & Preset Logic Control

Logic for the programmable register's clear and preset functions is controlled by the DATA3, LABCTRL1, and LABCTRL2 inputs to the LE. The clear and preset control structure of the LE asynchronously loads signals into a register. Either LABCTRL1 or LABCTRL2 can control the asynchronous clear. Alternatively, the register can be set up so that LABCTRL1 implements an asynchronous load. The data to be loaded is driven to DATA3; when LABCTRL1 is asserted, DATA3 is loaded into the register.

Table 15. 32-Bit FLEX 10K Device IDCODE *Note (1)*

Device	IDCODE (32 Bits)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer's Identity (11 Bits)	1 (1 Bit) (2)
EPF10K10, EPF10K10A	0000	0001 0000 0001 0000	00001101110	1
EPF10K20	0000	0001 0000 0010 0000	00001101110	1
EPF10K30, EPF10K30A	0000	0001 0000 0011 0000	00001101110	1
EPF10K40	0000	0001 0000 0100 0000	00001101110	1
EPF10K50, EPF10K50V	0000	0001 0000 0101 0000	00001101110	1
EPF10K70	0000	0001 0000 0111 0000	00001101110	1
EPF10K100, EPF10K100A	0000	0000 0001 0000 0000	00001101110	1
EPF10K130V	0000	0000 0001 0011 0000	00001101110	1
EPF10K250A	0000	0000 0010 0101 0000	00001101110	1

Notes:

- (1) The most significant bit (MSB) is on the left.
- (2) The least significant bit (LSB) for all JTAG IDCODEs is 1.

FLEX 10K devices include weak pull-ups on JTAG pins.



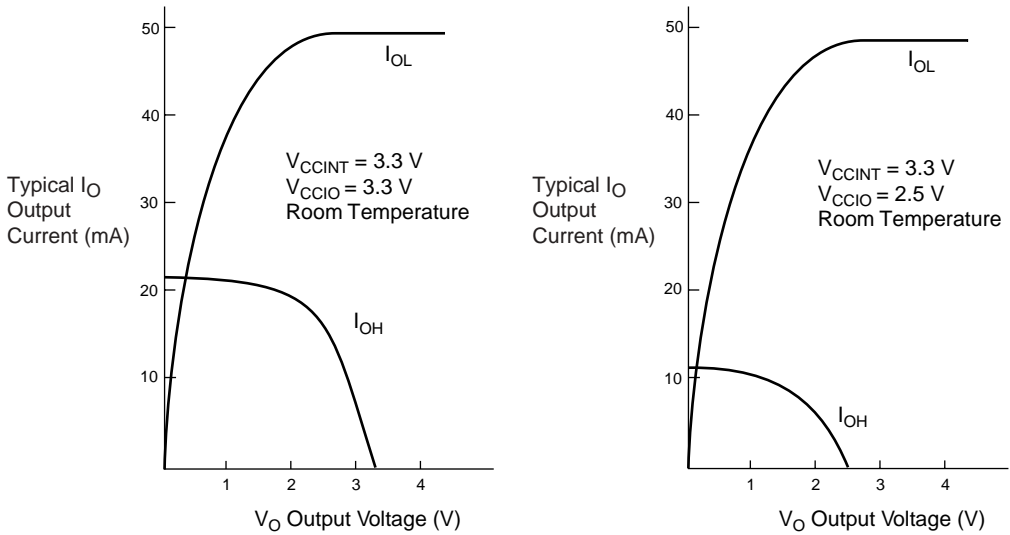
For more information, see the following documents:

- *Application Note 39 (IEEE 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Jam Programming & Test Language Specification*

Table 27. FLEX 10KA 3.3-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.30 (2.30)	2.70 (2.70)	V
V_I	Input voltage	(5)	-0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	°C
		For industrial use	-40	85	°C
T_J	Operating temperature	For commercial use	0	85	°C
		For industrial use	-40	100	°C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Figure 23. Output Drive Characteristics for EPF10K250A Device



Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (t_{CO})
- Interconnect delay ($t_{SAMEROW}$)
- LE look-up table delay (t_{LUT})
- LE register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Figures 25 through 27 show the delays that correspond to various paths and functions within the LE, IOE, and EAB timing models.

Figure 25. FLEX 10K Device LE Timing Model

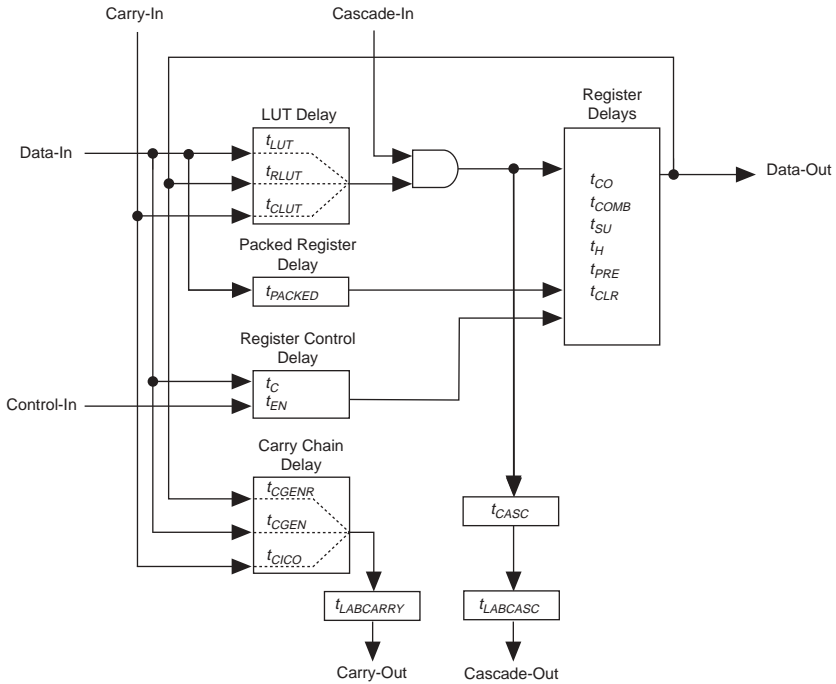


Table 42. EPF10K10 & EPF10K20 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Tables 48 through 56 show EPF10K30, EPF10K40, and EPF10K50 device internal and external timing parameters.

Table 48. EPF10K30, EPF10K40 & EPF10K50 Device LE Timing Microparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{LUT}		1.3		1.8	ns
t_{CLUT}		0.6		0.6	ns
t_{RLUT}		1.5		2.0	ns
t_{PACKED}		0.5		0.8	ns
t_{EN}		0.9		1.5	ns
t_{CICO}		0.2		0.4	ns
t_{CGEN}		0.9		1.4	ns
t_{CGENR}		0.9		1.4	ns
t_{CASC}		1.0		1.2	ns
t_C		1.3		1.6	ns
t_{CO}		0.9		1.2	ns
t_{COMB}		0.6		0.6	ns
t_{SU}	1.4		1.4		ns
t_H	0.9		1.3		ns
t_{PRE}		0.9		1.2	ns
t_{CLR}		0.9		1.2	ns
t_{CH}	4.0		4.0		ns
t_{CL}	4.0		4.0		ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_C		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_H	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 65. EPF10K100 Device IOE Timing Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		0.0		0.0		0.0	ns
t_{IOC}		0.5		0.5		0.7	ns
t_{IOCO}		0.4		0.4		0.9	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	5.5		5.5		6.7		ns
t_{IOH}	0.5		0.5		0.7		ns
t_{IOCLR}		0.7		0.7		1.6	ns
t_{OD1}		4.0		4.0		5.0	ns
t_{OD2}		6.3		6.3		7.3	ns
t_{OD3}		7.7		7.7		8.7	ns
t_{XZ}		6.2		6.2		6.8	ns
t_{ZX1}		6.2		6.2		6.8	ns
t_{ZX2}		8.5		8.5		9.1	ns
t_{ZX3}		9.9		9.9		10.5	ns
t_{INREG} without ClockLock or ClockBoost circuitry		9.0		9.0		10.5	ns
t_{INREG} with ClockLock or ClockBoost circuitry		3.0		–		–	ns
t_{IOFD}		8.1		8.1		10.3	ns
t_{INCOMB}		8.1		8.1		10.3	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Tables 78 through 84 show EPF10K130V device internal and external timing parameters.

Table 78. EPF10K130V Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.8		2.3	ns
t_{CLUT}		0.5		0.7		0.9	ns
t_{RLUT}		1.2		1.7		2.2	ns
t_{PACKED}		0.5		0.6		0.7	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.3		0.4		0.5	ns
t_{CGENR}		0.7		1.0		1.3	ns
t_{CASC}		0.9		1.2		1.5	ns
t_C		1.9		2.4		3.0	ns
t_{CO}		0.6		0.9		1.1	ns
t_{COMB}		0.5		0.7		0.9	ns
t_{SU}	0.2		0.2		0.3		ns
t_H	0.0		0.0		0.0		ns
t_{PRE}		2.4		3.1		3.9	ns
t_{CLR}		2.4		3.1		3.9	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 94. EPF10K30A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		5.5		6.5		8.5	ns
$t_{EABDATA2}$		1.1		1.3		1.8	ns
t_{EABWE1}		2.4		2.8		3.7	ns
t_{EABWE2}		2.1		2.5		3.2	ns
t_{EABCLK}		0.0		0.0		0.2	ns
t_{EABCO}		1.7		2.0		2.6	ns
$t_{EABBYPASS}$		0.0		0.0		0.3	ns
t_{EABSU}	1.2		1.4		1.9		ns
t_{EABH}	0.1		0.1		0.3		ns
t_{AA}		4.2		5.0		6.5	ns
t_{WP}	3.8		4.5		5.9		ns
t_{WDSU}	0.1		0.1		0.2		ns
t_{WDH}	0.1		0.1		0.2		ns
t_{WASU}	0.1		0.1		0.2		ns
t_{WAH}	0.1		0.1		0.2		ns
t_{WO}		3.7		4.4		6.4	ns
t_{DD}		3.7		4.4		6.4	ns
t_{EABOUT}		0.0		0.1		0.6	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.8		4.5		5.9		ns

Table 96. EPF10K30A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		3.9		4.4		5.1	ns
t_{DIN2LE}		1.2		1.5		1.9	ns
$t_{DIN2DATA}$		3.2		3.6		4.5	ns
$t_{DCLK2IOE}$		3.0		3.5		4.6	ns
$t_{DCLK2LE}$		1.2		1.5		1.9	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.3		2.4		2.7	ns
$t_{SAMECOLUMN}$		1.3		1.4		1.9	ns
$t_{DIFFROW}$		3.6		3.8		4.6	ns
$t_{TROWROWS}$		5.9		6.2		7.3	ns
$t_{LEPERIPH}$		3.5		3.8		4.1	ns
$t_{LABCARRY}$		0.3		0.4		0.5	ns
$t_{LABCASC}$		0.9		1.1		1.4	ns

Table 97. EPF10K30A External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		11.0		13.0		17.0	ns
t_{INSU} (2), (3)	2.5		3.1		3.9		ns
t_{INH} (3)	0.0		0.0		0.0		ns
t_{OUTCO} (3)	2.0	5.4	2.0	6.2	2.0	8.3	ns

Table 98. EPF10K30A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	4.2		4.9		6.8		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.4	2.0	6.2	2.0	8.3	ns
$t_{XZBIDIR}$		6.2		7.5		9.8	ns
$t_{ZXBIDIR}$		6.2		7.5		9.8	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Tables 99 through 105 show EPF10K100A device internal and external timing parameters.

Table 99. EPF10K100A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.0		1.2		1.4	ns
t_{CLUT}		0.8		0.9		1.1	ns
t_{RLUT}		1.4		1.6		1.9	ns
t_{PACKED}		0.4		0.5		0.5	ns
t_{EN}		0.6		0.7		0.8	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.6		0.7		0.8	ns
t_{CASC}		0.7		0.9		1.0	ns
t_C		0.9		1.0		1.2	ns
t_{CO}		0.2		0.3		0.3	ns
t_{COMB}		0.6		0.7		0.8	ns
t_{SU}	0.8		1.0		1.2		ns
t_H	0.3		0.5		0.5		ns
t_{PRE}		0.3		0.3		0.4	ns
t_{CLR}		0.3		0.3		0.4	ns
t_{CH}	2.5		3.5		4.0		ns
t_{CL}	2.5		3.5		4.0		ns

Table 101. EPF10K100A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.8		2.1		2.4	ns
$t_{EABDATA2}$		3.2		3.7		4.4	ns
t_{EABWE1}		0.8		0.9		1.1	ns
t_{EABWE2}		2.3		2.7		3.1	ns
t_{EABCLK}		0.8		0.9		1.1	ns
t_{EABCO}		1.0		1.1		1.4	ns
$t_{EABBYPASS}$		0.3		0.3		0.4	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	0.4		0.5		0.5		ns
t_{AA}		4.1		4.8		5.6	ns
t_{WP}	3.2		3.7		4.4		ns
t_{WDSU}	2.4		2.8		3.3		ns
t_{WDH}	0.2		0.2		0.3		ns
t_{WASU}	0.2		0.2		0.3		ns
t_{WAH}	0.0		0.0		0.0		ns
t_{WO}		3.4		3.9		4.6	ns
t_{DD}		3.4		3.9		4.6	ns
t_{EABOUT}		0.3		0.3		0.4	ns
t_{EABCH}	2.5		3.5		4.0		ns
t_{EABCL}	3.2		3.7		4.4		ns

Table 102. EPF10K100A Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.8		7.8		9.2	ns
$t_{EABRCCOMB}$	6.8		7.8		9.2		ns
$t_{EABRCREG}$	5.4		6.2		7.4		ns
t_{EABWP}	3.2		3.7		4.4		ns
$t_{EABWCCOMB}$	3.4		3.9		4.7		ns
$t_{EABWCREG}$	9.4		10.8		12.8		ns
t_{EABDD}		6.1		6.9		8.2	ns
$t_{EABDATACO}$		2.1		2.3		2.9	ns
$t_{EABDATASU}$	3.7		4.3		5.1		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	2.8		3.3		3.8		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	3.4		4.0		4.6		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	1.9		2.3		2.6		ns
t_{EABWAH}	0.0		0.0		0.0		ns
t_{EABWO}		5.1		5.7		6.9	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

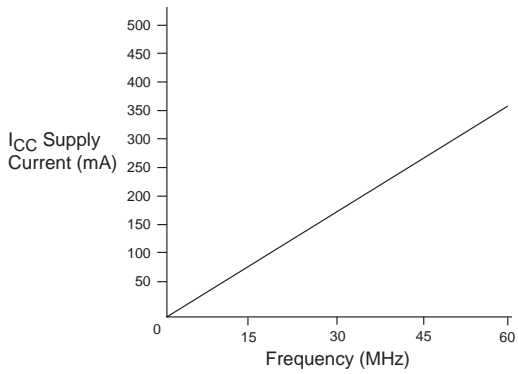
Tables 106 through 112 show EPF10K250A device internal and external timing parameters.

Table 106. EPF10K250A Device LE Timing Microparameters *Note (1)*

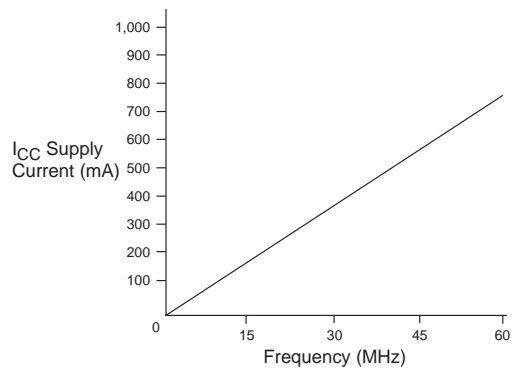
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.0		1.4	ns
t_{CLUT}		1.2		1.3		1.6	ns
t_{RLUT}		2.0		2.3		2.7	ns
t_{PACKED}		0.4		0.4		0.5	ns
t_{EN}		1.4		1.6		1.9	ns
t_{CICO}		0.2		0.3		0.3	ns
t_{CGEN}		0.4		0.6		0.6	ns
t_{CGENR}		0.8		1.0		1.1	ns
t_{CASC}		0.7		0.8		1.0	ns
t_C		1.2		1.3		1.6	ns
t_{CO}		0.6		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.7	ns
t_{SU}	1.2		1.4		1.7		ns
t_H	1.2		1.3		1.6		ns
t_{PRE}		0.7		0.8		0.9	ns
t_{CLR}		0.7		0.8		0.9	ns
t_{CH}	2.5		3.0		3.5		ns
t_{CL}	2.5		3.0		3.5		ns

Figure 32. $I_{CCACTIVE}$ vs. Operating Frequency (Part 1 of 3)

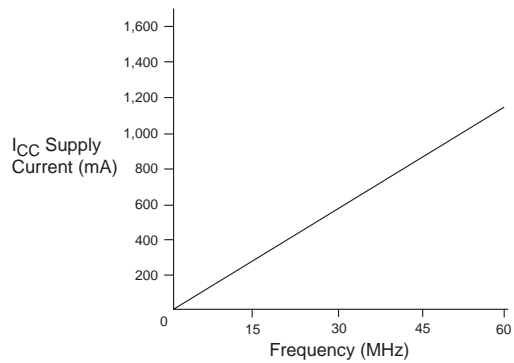
EPF10K10



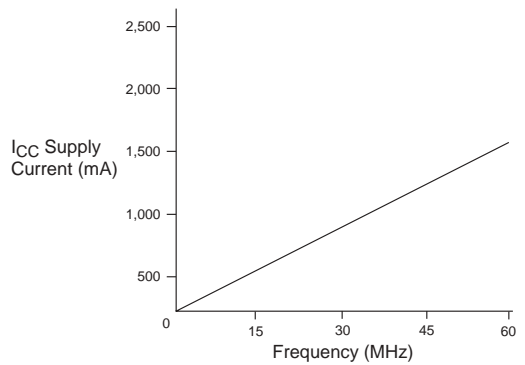
EPF10K20



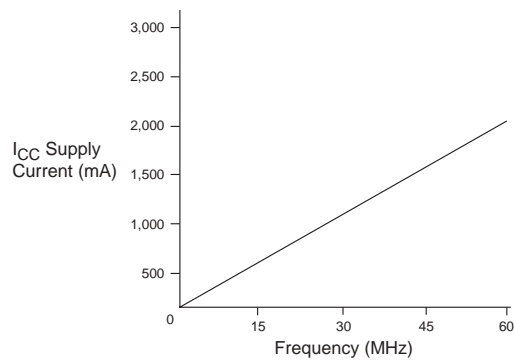
EPF10K30



EPF10K40



EPF10K50



EPF10K70

